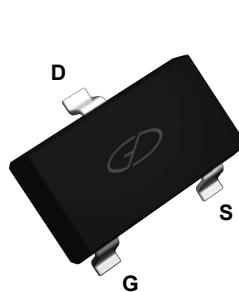
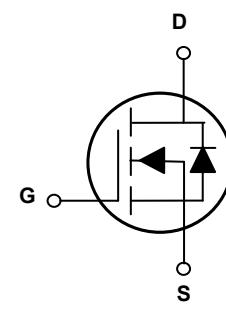


Main Product Characteristics

$V_{(BR)DSS}$	30V
$R_{DS(ON)}$	34mΩ (max.)
I_D	5.6A



SOT-23



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for high efficiency switched mode power supplies
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The SSF3324 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-to-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current, @ Steady-State ($T_A=25^\circ\text{C}$) ¹	I_D	5.6	A
Continuous Drain Current, @ Steady-State ($T_A=70^\circ\text{C}$)		4.5	A
Pulsed Drain Current ²	I_{DM}	23	A
Power Dissipation ($T_A=25^\circ\text{C}$)	P_D	1.15	W
Linear Derating Factor ($T_A=25^\circ\text{C}$)		0.012	W/ $^\circ\text{C}$
Junction-to-Ambient (PCB Mounted, Steady-State) ³	$R_{\theta JA}$	100	$^\circ\text{C}/\text{W}$
Operating Junction and Storage Temperature Range	T_J/T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	30	-	-	V
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS}=24\text{V}, V_{GS}=0\text{V}$	-	-	1	μA
		$T_J=125^\circ\text{C}$	-	-	50	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=12\text{V}$	-	-	100	nA
		$V_{DS}=0\text{V}, V_{GS}=-12\text{V}$	-	-	-100	
Static Drain-to-Source On-Resistance	$R_{DS(\text{ON})}$	$V_{GS}=4.5\text{V}, I_D=2\text{A}$	-	25	34	$\text{m}\Omega$
		$V_{GS}=2.5\text{V}, I_D=1.5\text{A}$	-	33	40	
		$V_{GS}=1.8\text{V}, I_D=1\text{A}$	-	51	60	
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.64	0.88	1.5	V
Dynamic and Switching Characteristics						
Input Capacitance	C_{iss}	$V_{GS}=0\text{V}, V_{DS}=15\text{V}, f=1\text{MHz}$	-	538	-	pF
Output Capacitance	C_{oss}		-	130	-	
Reverse Transfer Capacitance	C_{rss}		-	36	-	
Total Gate Charge	Q_g	$I_D=5.6\text{A}, V_{DS}=15\text{V}, V_{GS}=4.5\text{V}$	-	4.8	-	nC
Gate-to-Source Charge	Q_{gs}		-	1.2	-	
Gate-to-Drain ("Miller") Charge	Q_{gd}		-	1.7	-	
Turn-on Delay Time	$t_{\text{d(on)}}$	$V_{GS}=4.5\text{V}, V_{DS}=15\text{V}, R_{\text{GEN}}=2.8\Omega, R_L=15\Omega, I_D=1\text{A}$	-	12	-	nS
Rise Time	t_r		-	52	-	
Turn-Off Delay Time	$t_{\text{d(off)}}$		-	17	-	
Fall Time	t_f		-	10	-	
Source-Drain Ratings and Characteristics						
Continuous Source Current (Body Diode)	I_s	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	5.6	A
Diode Forward Voltage	V_{SD}	$I_s=2.5\text{A}, V_{GS}=0\text{V}$	-	-	1.2	V
Reverse Recovery Time	T_{rr}	$T_J=25^\circ\text{C}, I_F=5.0\text{A}, \frac{dI}{dt}=100\text{A}/\mu\text{s}$	-	10.8	-	nS
Reverse Recovery Charge	Q_{rr}		-	5.4	-	uC

Notes:

1. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
2. Repetitive rating; pulse width limited by max. junction temperature.
3. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

Typical Electrical and Thermal Characteristic Curves

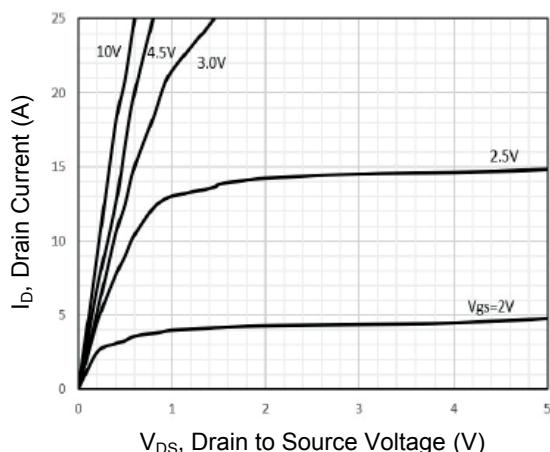


Figure 1. Typical Output Characteristics

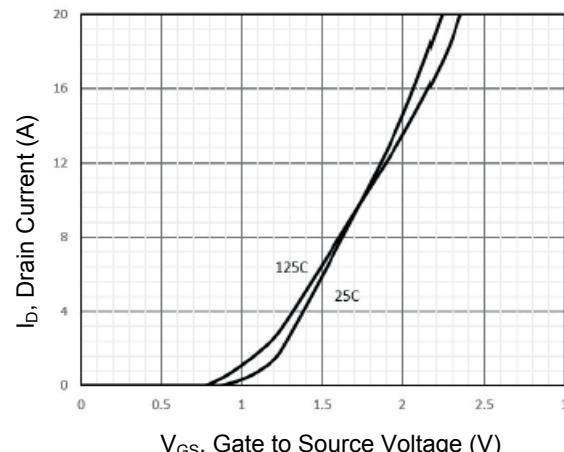


Figure 2. Typical Transfer Characteristics

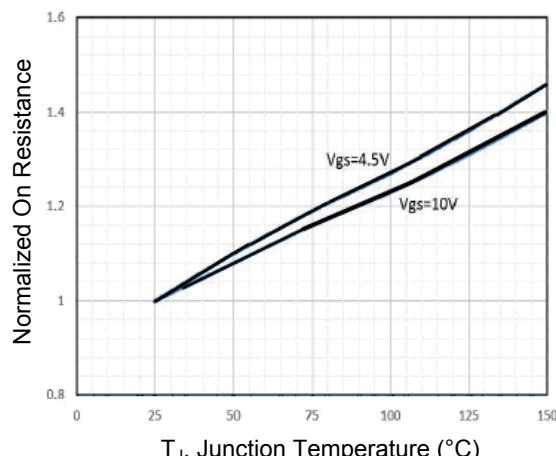


Figure 3. Normalized $R_{DS(ON)}$ vs. T_J

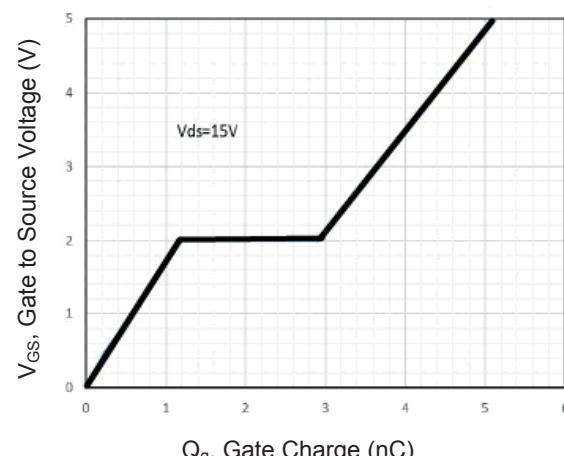


Figure 4. Gate Charge

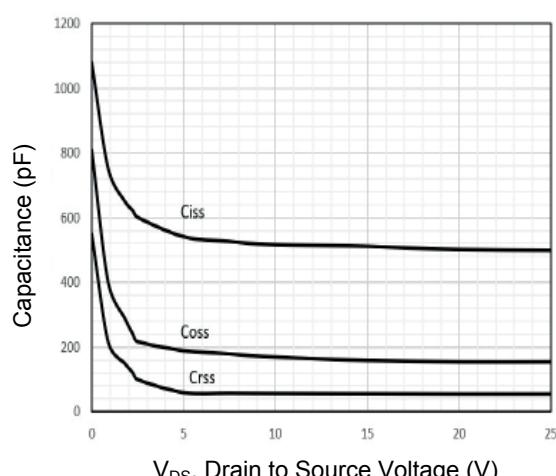


Figure 5. Capacitance Characteristics

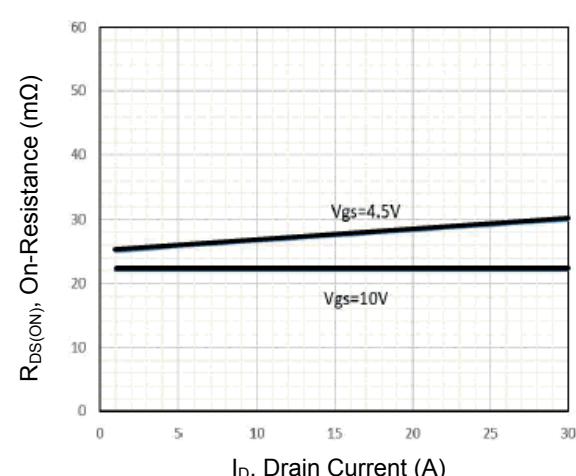
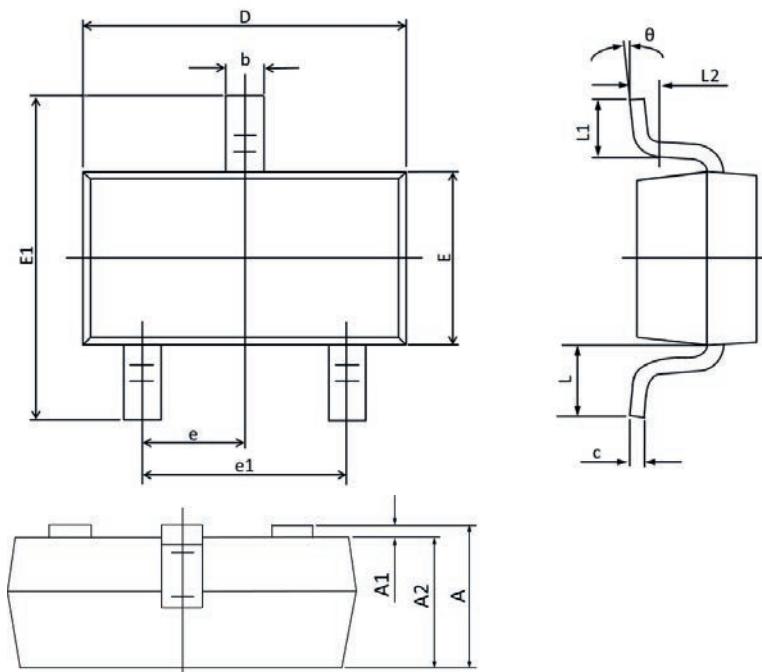


Figure 6. Typical Drain-Source on-Resistance

Package Outline Dimensions (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.250	1.840	0.049	0.072
E1	2.250	2.550	0.089	0.100
e	0.95 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.55 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
L2	0.25 TYP.		0.01 TYP.	
θ	0°	8°	0°	8°

Order Information

Device	Package	Marking	Carrier	Quantity
SSF3324	SOT-23	3324	Tape & Reel	3,000 pcs / Reel

For more information, please contact us at: inquiry@goodarksemi.com